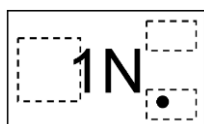
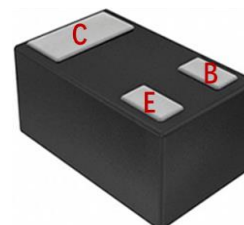
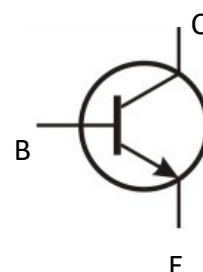


GP3904Y3 Transistor(NPN)

Feature

- Switching Transistor
- Collector-Emitter Voltage $V_{CE}=40V$
- Collector Current $I_C=0.2A$

Marking:

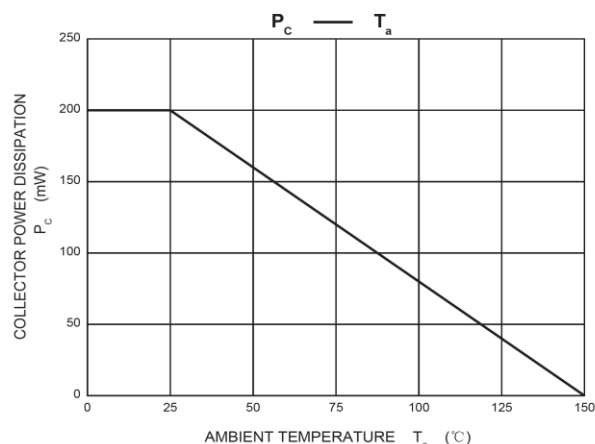
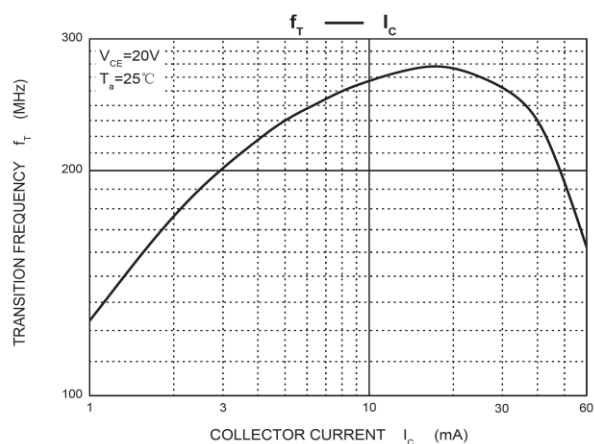
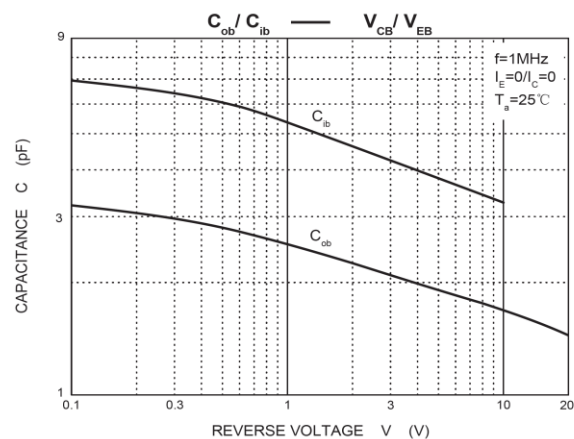
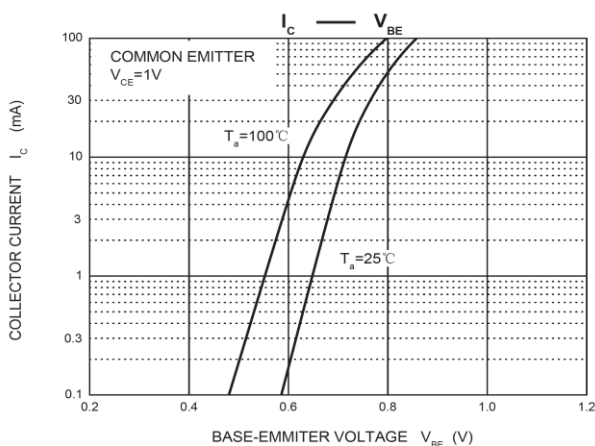
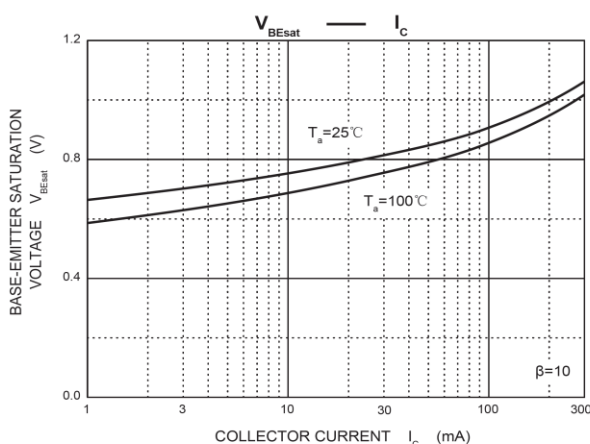
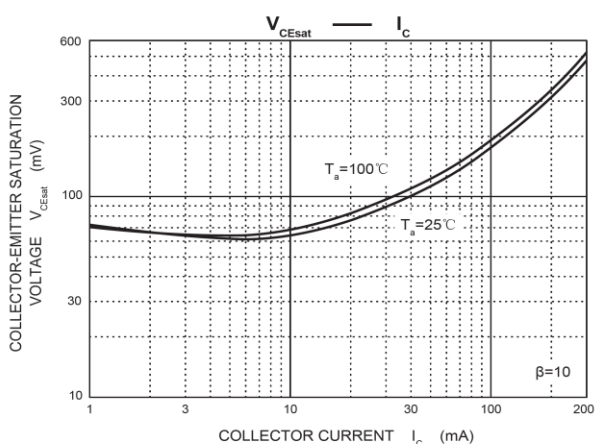
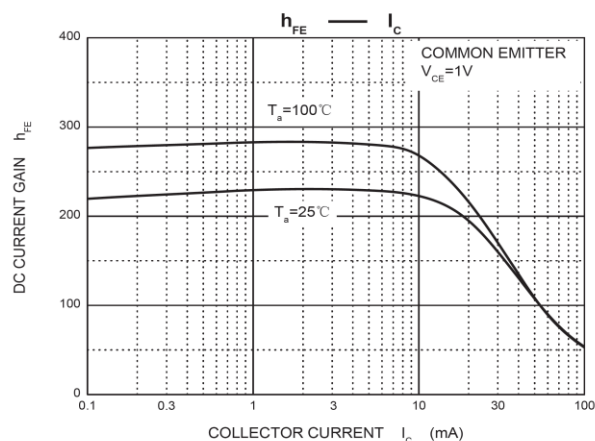
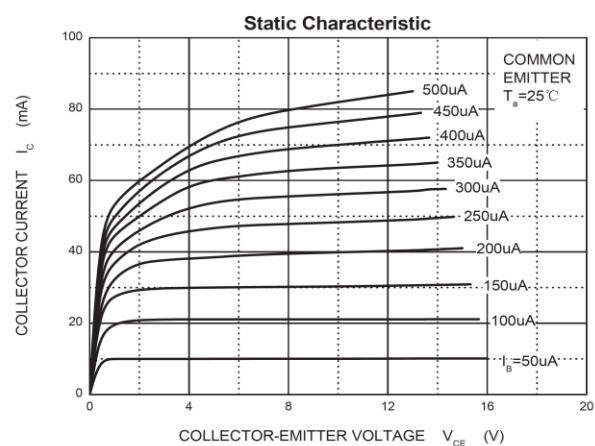

DFN1006-3L

Schematic diagram


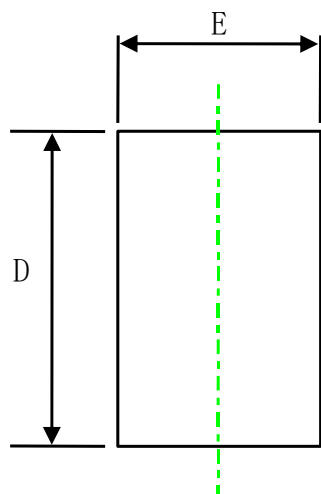
MAXIMUM RATINGS ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Continuous Collector Current	I_C	0.2	A
Power Dissipation	P_D	0.1	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	1250	$^{\circ}C/W$

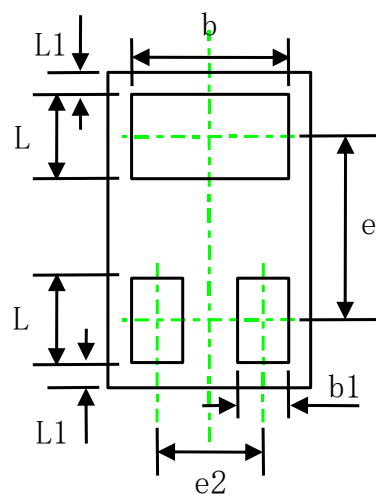
ELECTRICAL CHARACTERISTICS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	60		V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	40		V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}, I_C = 0$	6		V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = 60\text{V}, I_E = 0$		100	nA
Collector Cut-Off Current	I_{CEX}	$V_{CE} = 30\text{V}, V_{EB(off)} = 3\text{V}$		50	nA
Emitter Cut-Off Current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$		100	nA
DC Current Gain	h_{FE1}	$V_{CE} = 1\text{V}, I_C = 0.1\text{mA}$	40		
	h_{FE2}	$V_{CE} = 1\text{V}, I_C = 1\text{mA}$	70		
	h_{FE3}	$V_{CE} = 1\text{V}, I_C = 10\text{mA}$	100	300	
	h_{FE4}	$V_{CE} = 1\text{V}, I_C = 50\text{mA}$	60		
	h_{FE5}	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	30		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$		0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$		0.95	V
Transition Frequency	f_T	$V_{CE} = 20\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$	300		MHz
Delay Time	t_d	$V_{CC} = 3\text{V}, I_C = 10\text{mA},$ $V_{BE(off)} = 0.5\text{V}, I_{B1} = 1\text{mA}$		35	ns
Rise Time	t_r			35	ns
Storage Time	t_s	$V_{CC} = 3\text{V}, I_C = 10\text{mA},$ $I_{B1} = I_{B2} = 1\text{mA}$		200	ns
Fall Time	t_f			50	ns

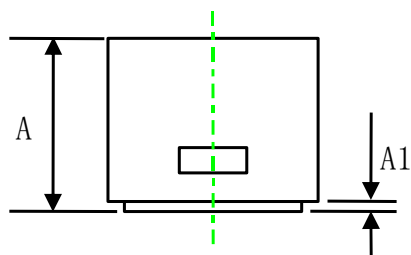
Typical Characteristics


DFN1006-3L Package Information


TOP VIEW
[顶视图]



BOTTOM VIEW
[底视图]



SIDE VIEW
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.550	0.016	0.022
A1	0.000	0.050	0.000	0.002
D	0.950	1.050	0.037	0.041
E	0.550	0.650	0.022	0.026
b	0.400	0.600	0.016	0.024
e	0.65 TYP		0.026 TYP	
e2	0.35 TYP		0.014 TYP	
L1	0.05 REF		0.002 REF	
L	0.200	0.300	0.008	0.012
b1	0.100	0.200	0.004	0.008

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.